



LED1050G-03

- Infrared LED
- 1050 nm, 15 mW
- Chip: GaAs, 300 x 300 μm
- 5 mm Clear Molding, Epoxy Resin
- Viewing Angle: 24°



Description



LED1050G-03 contains one GaAs LED chip die mounted on a lead frame hermetically sealed with a clear epoxy lens.

On forward bias, it emits a power radiation of typical **15 mW** at a peak wavelength at **1050 nm**.

Maximum Ratings ($T_{\text{CASE}}=25^{\circ}\text{C}$)

Parameter	Symbol	Values		Unit
		Min.	Max.	
Power Dissipation	P_D		130	mW
Forward Current	I_F		100	mA
Pulse Forward Current *1	I_{FP}		1000	mA
Reverse Voltage	V_F		5	V
Thermal Resistance	R_{THJA}		300	K/W
Junction Temperature	T_J		120	$^{\circ}\text{C}$
Operating Temperature	T_{CASE}	- 40	+ 100	$^{\circ}\text{C}$
Storage Temperature	T_{STG}	- 40	+ 100	$^{\circ}\text{C}$
Lead Solder Temperature *2	T_{SLD}		+ 265	$^{\circ}\text{C}$

*1 duty=1%, pulse width = 10 μs

*2 must be completed within 3 seconds

Electro-Optical Characteristics ($T_{\text{CASE}}=25^{\circ}\text{C}$)

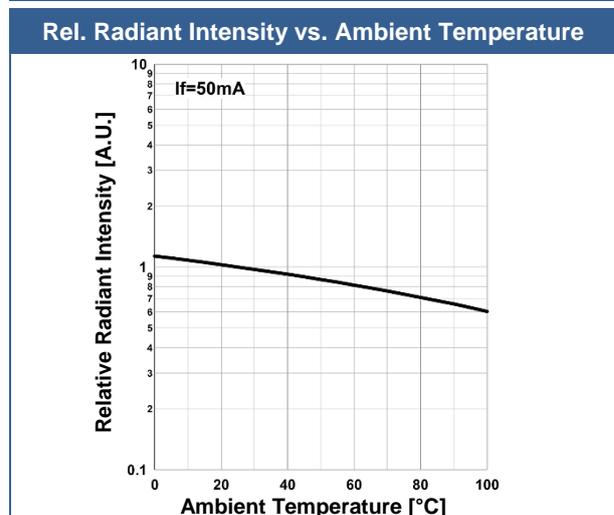
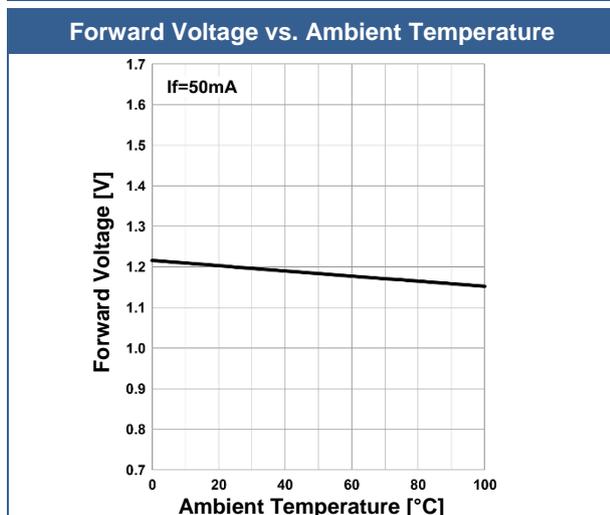
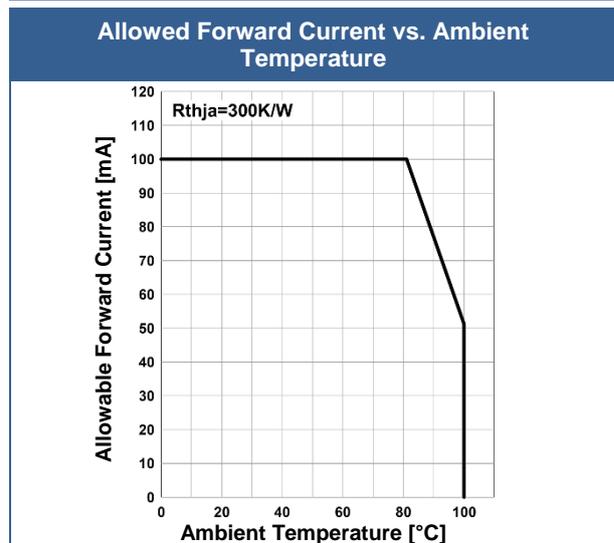
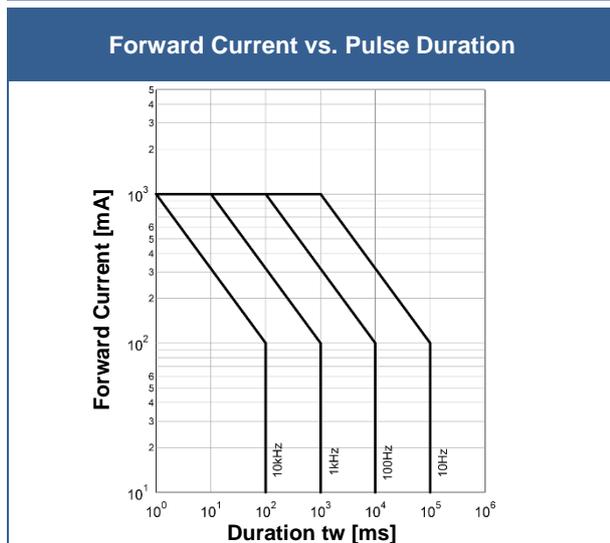
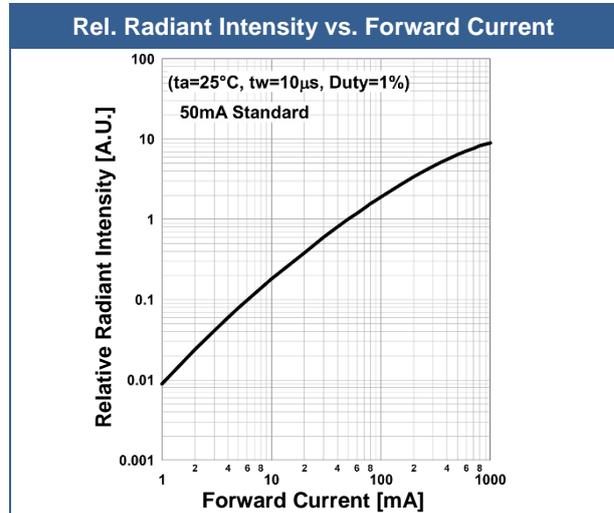
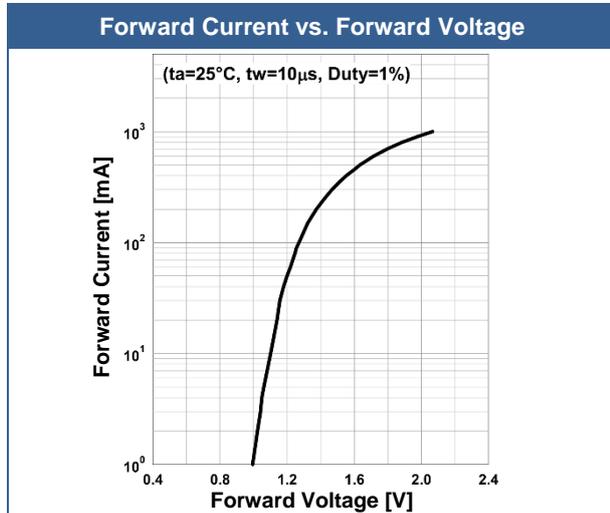
Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Peak Wavelength	λ_P	$I_F=50\text{mA}$	1000		1100	nm
Half Width	$\Delta\lambda$	$I_F=50\text{mA}$		42		nm
Forward Voltage	V_F	$I_F=50\text{mA}$		1.2	1.3	V
	V_{FP}	$I_{FP}=500\text{mA}$		2.1		
Radiated Power *1	P_O	$I_F=50\text{mA}$		15		mW
		$I_{FP}=500\text{mA}$		130		
Radiant Intensity *2	I_E	$I_F=50\text{mA}$		73		mW/sr
		$I_{FP}=500\text{mA}$		650		
Viewing Angle	φ	$I_F=50\text{mA}$		24		deg.
Rise Time	t_R	$I_F=50\text{mA}$		30		ns
Fall Time	t_F	$I_F=50\text{mA}$		30		ns

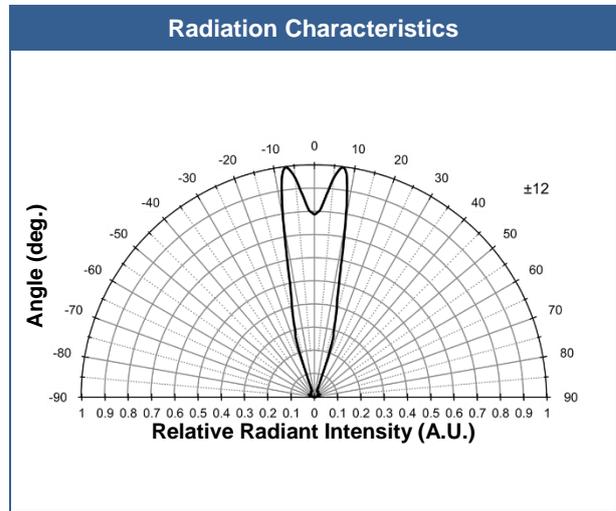
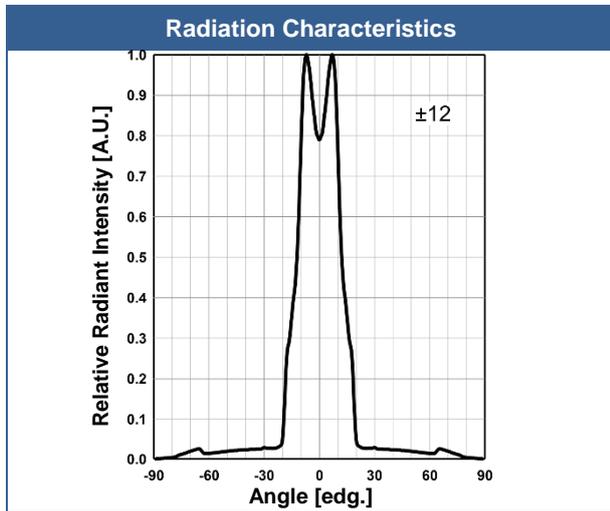
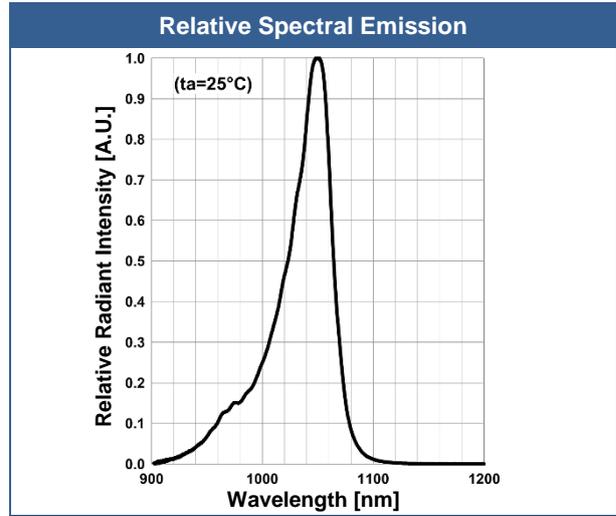
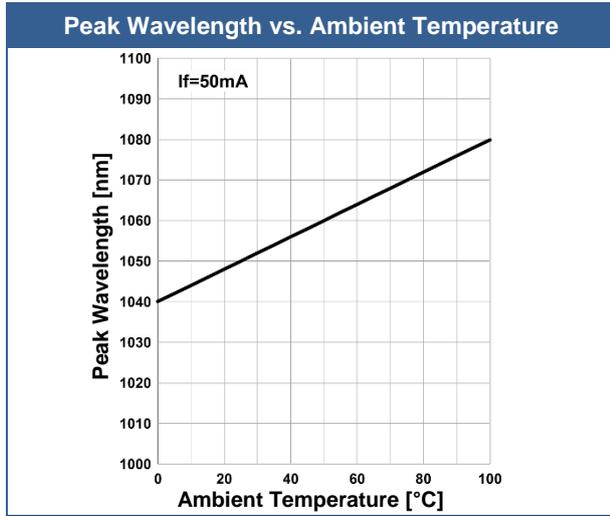
*1 measured by G8370-85

*2 measured by Ando Optical Multi Meter AQ2140 & AQ2742

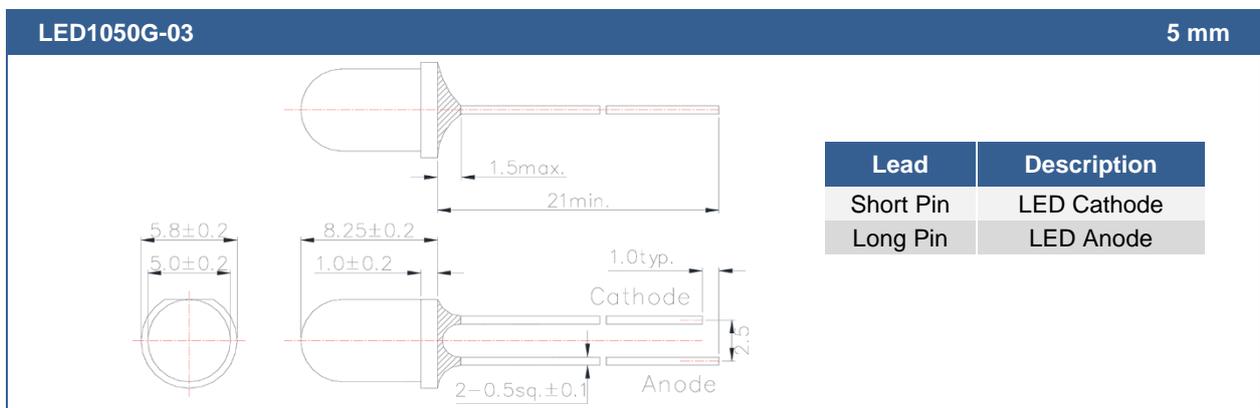


Typical Performance Curves





Outline Dimensions



All Dimensions in mm

